Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
-30V	7.5mΩ @ V_{GS} = -10V	-12A
	10.2mΩ @ V_{GS} = -4.5V	-10A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

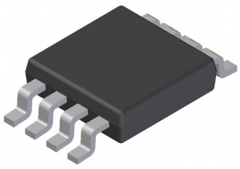
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

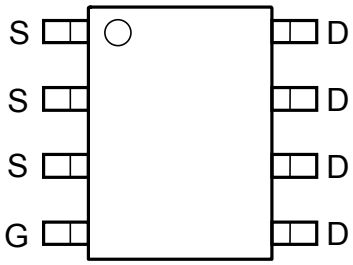
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram below
- Terminals: Finish — Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (approximate)

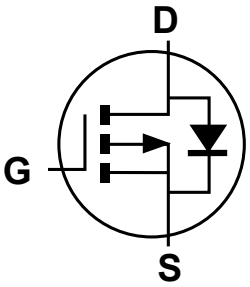
SO-8



Top View



Top View
Pin-out



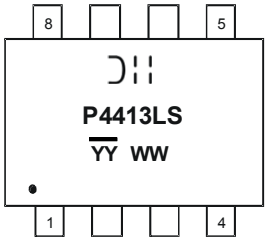
Equivalent Circuit

Ordering Information (Note 4)

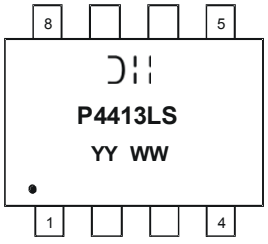
Part Number	Case	Packaging
DMG4413LSS-13	SO-8	2500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

= Manufacturer's Marking
P4413LS = Product Type Marking Code
YYWW = Date Code Marking
YY or $\overline{YY}$ = Year (ex: 13 = 2013)
WW = Week (01 - 53)
$\underline{YY}$ = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{YY}$ = Date Code Marking for CAT (Chengdu Assembly/ Test site)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-12 -10	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-22 -17	A
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-10 -8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-18 -14	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	-100	A
Maximum Body Diode continuous Current			I_S	-4	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.7	W
	T_A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	74	°C/W
	t<10s		22	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.2	W
	T_A = +70°C		1.4	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	56	°C/W
	t<10s		17	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	2.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.1	1.6	-2.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— —	6.3 7.9	7.5 10.2	mΩ	V_{GS} = -10V, I_D = -13A V_{GS} = -4.5V, I_D = -10A
Forward Transconductance	g_{fs}	—	26	—	S	V_{DS} = -15V, I_D = -13A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.0	V	V_{GS} = 0V, I_S = -2.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	4965	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	1487	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	711	—	pF	
Gate Resistance	R_G	—	7.3	—	Ω	V_{DS} = 0V, V_{GS} = 0V f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_G	—	46	—	nC	V_{DS} = -15V, V_{GS} = -5V I_D = -13A
Gate-Source Charge	Q_{GS}	—	17	—		
Gate-Drain Charge	Q_{GD}	—	16	—		
Turn-On Delay Time	$t_{d(on)}$	—	15	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_G = 6.0Ω
Rise Time	t_r	—	9	—		
Turn-Off Delay Time	$t_{d(off)}$	—	160	—		
Fall Time	t_f	—	66	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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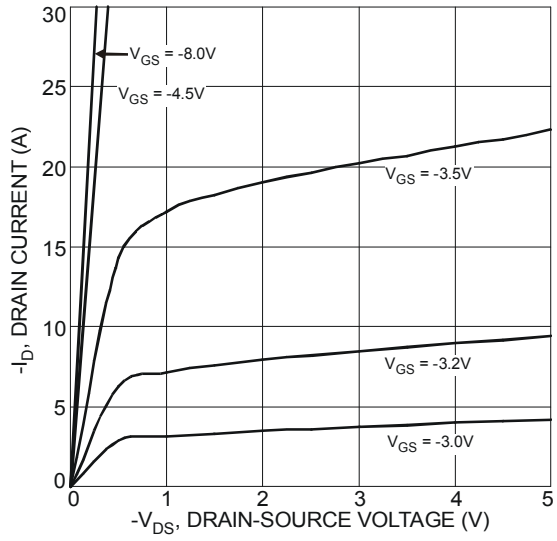

Fig. 1 Typical Output Characteristic

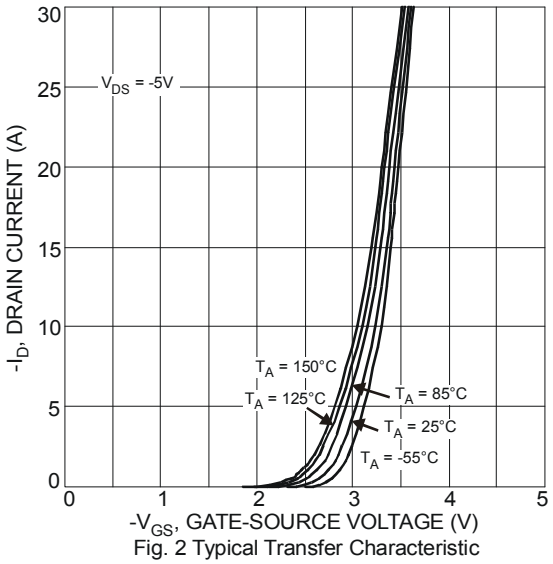

Fig. 2 Typical Transfer Characteristic

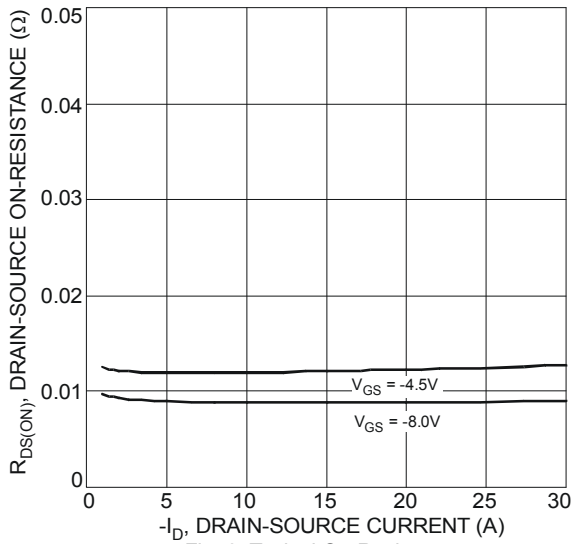

Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

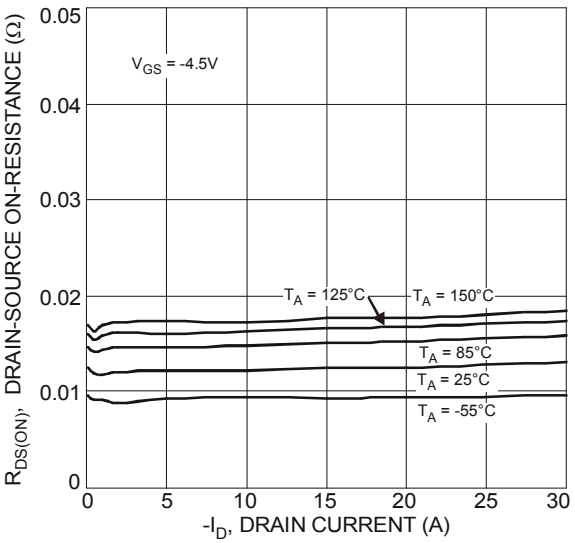

Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

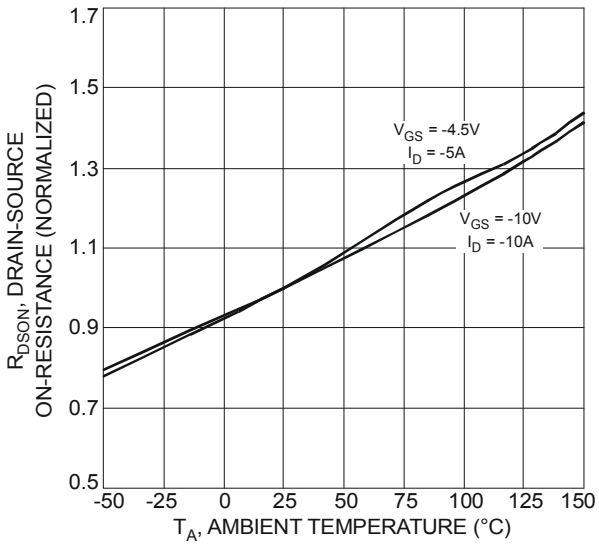

Fig. 5 On-Resistance Variation with Temperature

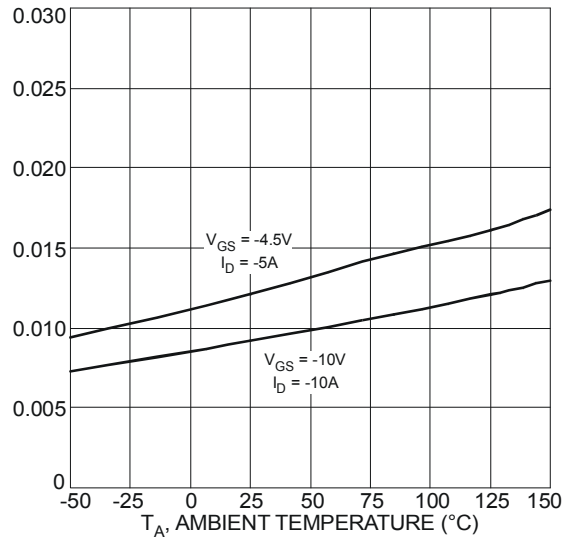

Fig. 6 On-Resistance Variation with Temperature

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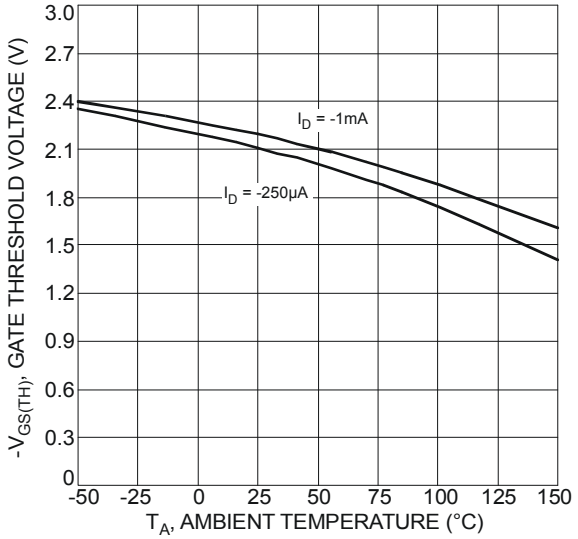


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

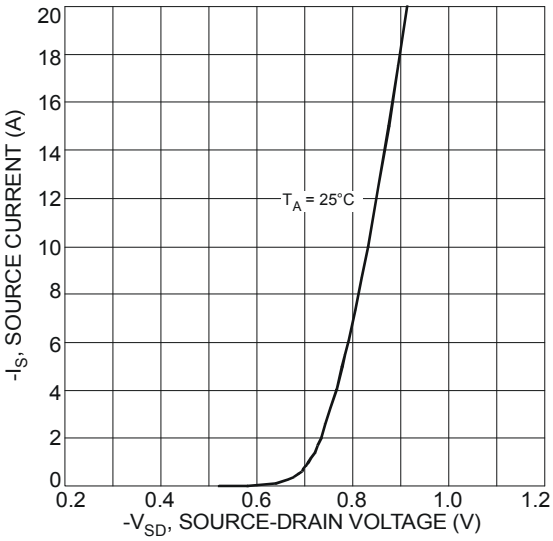


Fig. 8 Diode Forward Voltage vs. Current

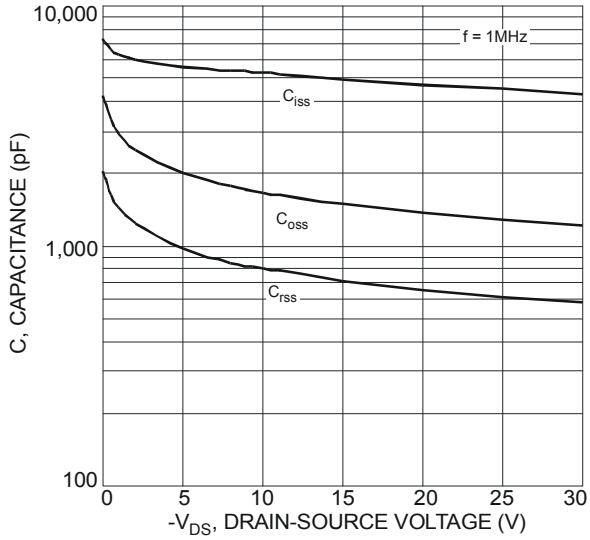
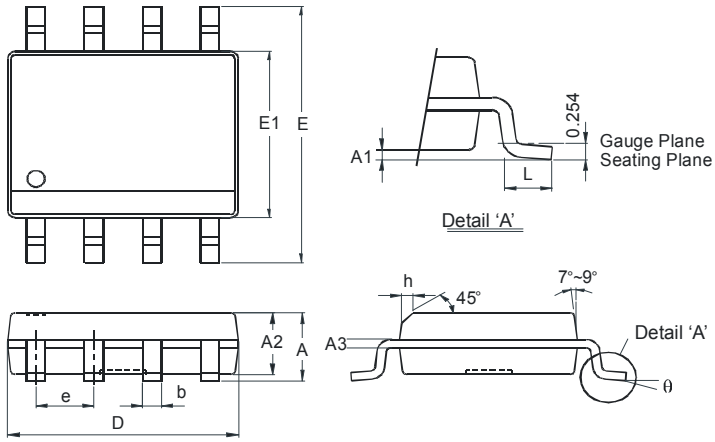


Fig. 9 Typical Total Capacitance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

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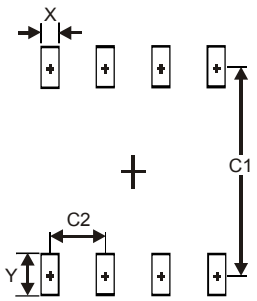
Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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